EDCON COMPONENTS
A MEMBER OF EDCON-GROUP

DL5711
DL6263

Small Signal Schottky Diodes

Features

- For general purpose applications
- These diodes are also available in the DO-35 case with type designation 1N5711 and 1N6263, in the Micro-MELF case with type designation MCL5711 and MCL6263.
- Lead Free Finish/RoHS Compliant(Note 1) ("P" Suffix designates Compliant. See ordering information)

Maximum Ratings

Repetitive Peak Reverse Voltage DL5711 DL6263	V_R	 70V 60V	
Maximum Forward Surge Current	I_{FSM}	2.0A	tp<10uS, T_A=25°C
Power Dissipation	P_{TOT}	400mW*	
Junction Temperature	T_J	125°C	
Storage Temperature Range	T_{STG}	-55~+150°C	

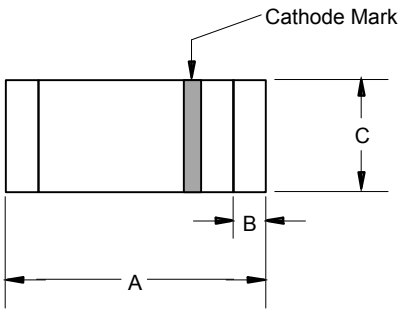
* Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics @ 25°C Unless Otherwise Specified

Maximum Forward Voltage	V_F	0.41V 1.0V	I_F = 1.0mA I_F = 15mA
Minimum Reverse Breakdown voltage DL5711 DL6263	V_R	 70V 60V	
Maximum Leakage current	I_R	200nA	V_R=50V
Maximum Junction Capacitance	C_J	2.0pF	V_R=0, f=1MHz
Maximum Reverse recovery time	t_{rr}	1.0ns	I_F=5.0mA , I_R=5.0mA ,
Maximum Thermal resistance junction to Ambient Air	$R_{\theta JA}$	0.3K/ W	

Note:1.Lead in Glass Exemption Applied, see EU Directive Annex 5.

MINIMELF



DIMENSION					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.134	.142	3.40	3.60	
B	.008	.016	0.20	0.40	
C	.055	.059	1.40	1.50	

SUGGESTED SOLDER PAD LAYOUT

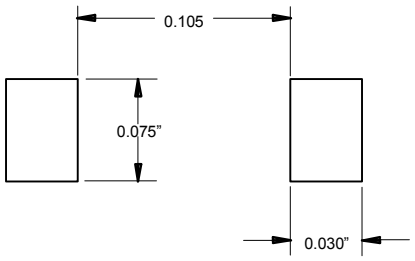


Fig.1 Typical variation of fwd. current vs forward. voltage for primary conduction through the Schottky barrier

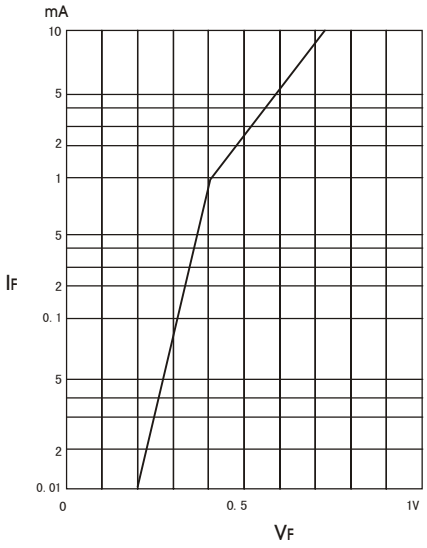


Fig.2 Typical forward conduction curve of combination Schottky barrier and PN junction guard ring

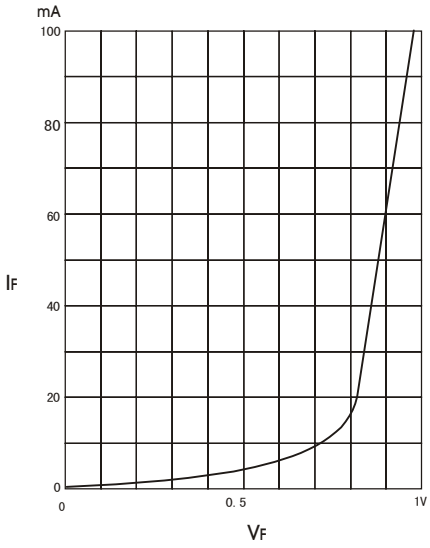


Fig.3 Typical variation of reverse current at various temperatures

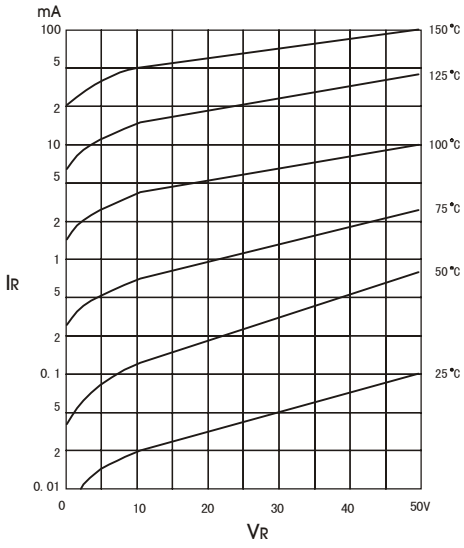
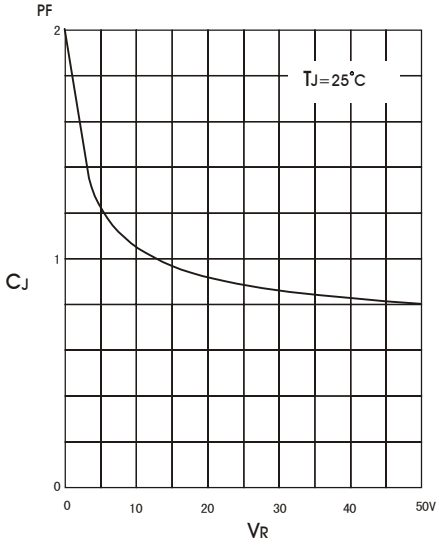


Fig.4 Typical capacitance curve as a function of reverse voltage



Ordering Information

Device	Packing
(Part Number)-TP	Tape&Reel;2.5Kpcs/Reel